

GD54/74HC365, GD54/74HCT365

HEX 3-STATE NONINVERTING BUFFERS

General Description

These devices are identical in pinout to the 54/74LS365. They have high drive current which enable high speed operation even when driving large bus capacitances. The HC/HCT 365 and HC/HCT 367 have noninverting outputs, while the HC/HCT 366 and HC/HCT 368 have inverting outputs. The HC/HCT 365 and HC/HCT 366 have two 3-state control inputs which are NORed together to control all 6 Gates. The HC/HCT 367 and HC/HCT 368 have two output enables, where one enable controls 4 gates and the other controls the remaining 2 gates. These devices are characterized for operation over wide temperature ranges to meet industry and military specifications.

Features

- Low Power consumption characteristic of CMOS devices
- Output drive capability: 15 LS TTL Loads Min.
- Operating speed superior to LS TTL
- Wide operating voltage range: for HC 2 to 6 volts for HCT 4.5 to 5.5 volts
- Low input current: 1 μ A Max.
- Low quiescent current: 80 μ A Max. (74HC)
- High noise immunity characteristic of CMOS
- Diode protection on all inputs

Logic Symbol

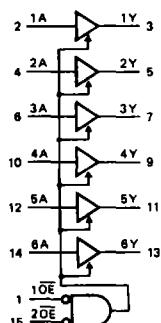
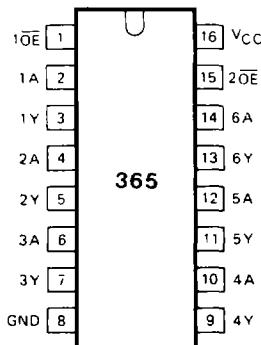


Fig. 1 Logic Symbol

Pin Configuration



suffix-blank Plastic Dual In Line Package
suffix-J Ceramic Dual In Line Package
suffix-D Small Outline Package

Function Table

INPUTS		OUTPUT	
1 \bar{OE}	2 \bar{OE}	nA	nY
L	L	L	L
L	L	H	H
X	H	X	Z
H	X	X	Z

H = HIGH voltage level

L = LOW voltage level

X = don't care

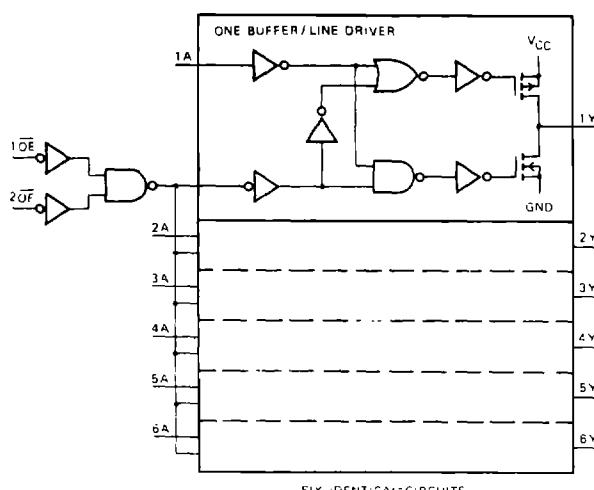
Z = high impedance OFF-state

Absolute Maximum Ratings

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CC}	DC Supply voltage		-0.5	+7	V
$I_{IK} I_{OK}$	DC input or output diode current	for $V_I < -0.5$ or $V_O > V_{CC} + 0.5V$		20	mA
I_O	DC output source or sink current	for $-0.5V < V_O < V_{CC} + 0.5V$		35	mA
I_{CC}	DC V_{CC} or GND current			70	mA
T_{ST}	Storage temperature range		-65	150	°C
P_D	Power dissipation per package	above +70°C degrade linearly with 8mW/K		500	mW
T_L	Lead temperature	At distance 1.16 ± 1.32 in from case for 60 sec(CERAMIC) 10 sec(PLASTIC)		300 260	°C

Recommended Operating Conditions

CHARACTERISTIC	LIMITS		UNITS
	MIN	MAX	
Supply-Voltage Range V_{CC} GD54/74HC Types GD54/74HCT Types	2 4.5	6 5.5	V
DC Input or Output Voltage V_I, V_O	0	V_{CC}	V
Operating Temperature T_A GD74 Types GD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall times t_r, t_f GD54/74HC Types at 2V at 4.5V at 6V GD54/74HCT Types at 4.5V		1000 500 400 500	ns

Logic Diagram**Fig. 2** Logic diagram

GD54/74HC365, GD54/74HCT365

DC Electrical Characteristics for HC

SYMBOL	PARAMETER	TEST CONDITION	V _{CC} (V)	T _A =25°C			GD74HC365		GD54HC365		UNIT
				MIN	TYP	MAX	MIN.	MAX	MIN.	MAX	
V _{IH}	HIGH level input Voltage		2.0 4.5 6.0	1.5 3.15 4.2			1.5 3.15 4.2		1.5 3.15 4.2		V
V _{IL}	LOW level input voltage		2.0 4.5 6.0			0.3 0.9 1.2		0.3 0.9 1.2		0.3 0.9 1.2	V
V _{OH}	HIGH level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OH} =-20μA	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0		1.9 4.4 5.9		1.9 4.4 5.9	V
			I _{OH} =-6mA	4.5 6.0	3.98 5.48	4.3 5.2		3.84 5.34		3.7 5.2	
			I _{OH} =-7.8mA								
V _{OL}	LOW level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OL} =20μA	2.0 4.5 6.0			0.1 0.1 0.1		0.1 0.1 0.1		V
			I _{OL} =6mA	4.5 6.0		0.17 0.15	0.26 0.26		0.33 0.33		
			I _{OL} =7.8mA							0.4 0.4	
I _{IN}	Input leakage Current	V _{IN} =V _{CC} or GND	6.0			0.1		1.0		1.0	μA
I _{OZ}	Three-State leakage current	V _{IN} =V _{IH} or V _{IL}	V _O =V _{CC} or GND	6.0		0.01	0.5		5.0		10.0 μA
I _{CC}	Quiescent Supply Current	V _{IN} =V _{CC} or GND I _{out} =0μA	6.0			8		80		160	μA

DC Electrical Characteristics for HCT

SYMBOL	PARAMETER	TEST CONDITION	V _{CC} (V)	T _A =25°C			GD74HCT365		GD54HCT365		UNIT
				MIN	TYP	MAX	MIN.	MAX.	MIN.	MAX.	
V _{IH}	HIGH level input Voltage		4.5 to 5.0	2.0			2.0		2.0		V
V _{IL}	LOW level input voltage		4.5 to 5.5			0.8		0.8		0.8	V
V _{OH}	HIGH level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OH} =-20μA	4.5	4.4	4.5		4.4		4.4	V
			I _{OH} =-6mA	4.5	3.98	4.3		3.84		3.7	
V _{OL}	LOW level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OL} =20μA	4.5			0.1		0.1		V
			I _{OL} =6mA	4.5		0.17	0.26		0.33		
I _{IN}	Input leakage Current	V _{IN} =V _{CC} or GND	5.5			0.1		1.0		1.0	μA
I _{OZ}	Three-State leakage current	V _{IN} =V _{IH} or V _{IL}	V _O =V _{CC} or GND	5.5		0.01	0.5		5.0		10.0 μA
I _{CC}	Quiescent Supply Current	V _{IN} =V _{CC} or GND I _{out} =0μA	5.5			8		80		160	μA

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AC Characteristics for HC, $t_r=t_f=6\text{ ns}$ $C_L=50\text{ pF}$

SYMBOL	PARAMETER	V_{CC} (V)	$T_A=25^\circ\text{C}$			GD74HC365		GD54HC365		UNIT
			MIN.	Typ.	MAX.	MIN.	MAX.	MIN.	MAX.	
t_{PLH}	Propagation Delay Time nA to nY	2.0		30	90			120		140
		4.5		10	19			24		29
		6.0		9	16			20		25
t_{PZH}	3-state Output Enable Time $n\overline{OE}$ to nY	2.0		40	140			180		210
		4.5		15	30			38		45
		6.0		12	25			32		38
t_{PHZ}	3-state Output Disable Time $n\overline{OE}$ to nY	2.0		40	140			180		210
		4.5		15	30			38		45
		6.0		12	25			32		38
t_{TLH}	Output Transition Time	2.0		15	60			75		90
		4.5		6	12			15		18
		6.0		5	10			13		15

AC Characteristics for HCT: $t_r=t_f=6\text{ ns}$ $C_L=50\text{ pF}$

SYMBOL	PARAMETER	V_{CC} (V)	$T_A=25^\circ\text{C}$			GD74HCT365		GD54HCT365		UNIT
			MIN.	Typ.	MAX.	MIN.	MAX.	MIN.	MAX.	
t_{PLH}	Propagation Delay Time nA to nY	4.5		12	22			26		30
										ns
t_{PZH}	3-state Output Enable Time $n\overline{OE}$ to nY	4.5		16	32			40		46
										ns
t_{PHZ}	3-state Output Disable Time $n\overline{OE}$ to nY	4.5		16	32			40		46
										ns
t_{TLH}	Output Transition Time	4.5		7	12			15		18
										ns

AC Waveforms

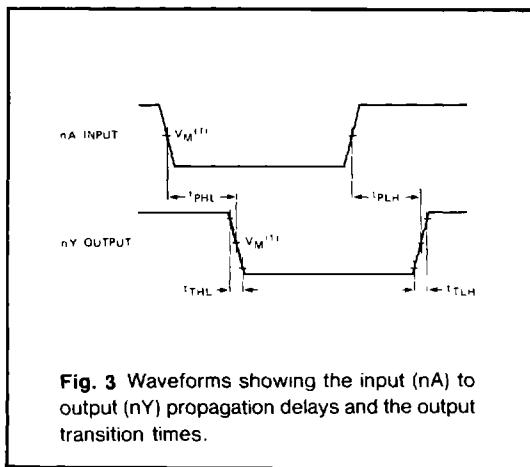


Fig. 3 Waveforms showing the input (nA) to output (nY) propagation delays and the output transition times.

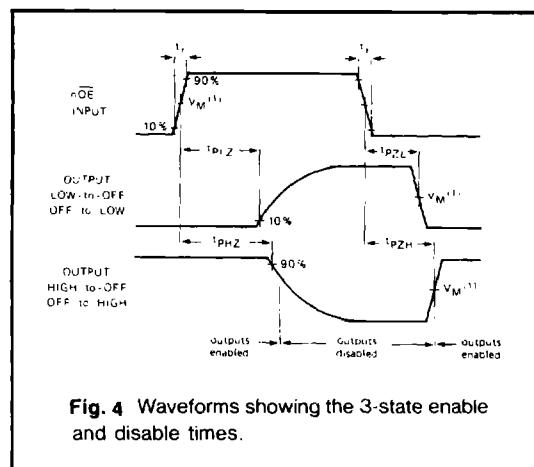


Fig. 4 Waveforms showing the 3-state enable and disable times.